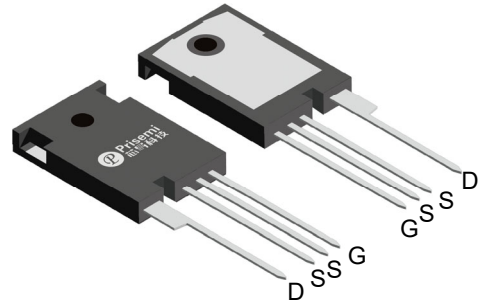


Description

MOSFET Product Summary

$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
1200	13 m Ω @ $V_{GS}=18V$	175



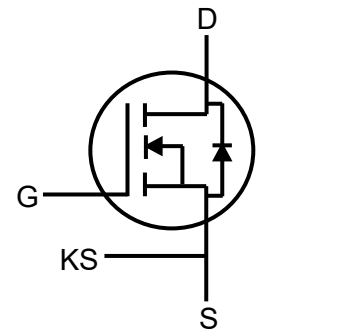
TO-247-4L (Top View)

Feature

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low $R_{DS(on)}$
- Avalanche Ruggednes

Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC-DC Converters
- Battery Chargers



Schematic diagram

Absolute maximum rating@25°C

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	1200	V
Gate-Source Voltage (Absolute maximum values)		V_{GSmax}	-8/+22	V
Gate-Source Voltage (Recommended operational values)		V_{GSop}	-4/+18	V
Continuous Drain Current	$T_C=25^\circ C$	I_D	175	A
	$T_C=100^\circ C$		125	
Pulsed drain current (Puls width tp limited by Tjmax)		I_{DM}	360	A
Power dissipation	$T_C=25^\circ C$	P_{tot}	833	W
	$T_C=100^\circ C$		416	
Operating Junction Temperature		T_J	-40 to +175	°C
Storage Temperature		T_{STG}	-40 to +175	°C

Thermal Resistance

Parameter	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.18	°C/W

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units	
Statistic Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 100μA	1200	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 1200V, V _{GS} = 0V T _J =175°C	-	1	-	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = 18V, V _{DS} = 0V	-	-	250	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 35mA	2	2.8	4	V	
		V _{DS} = V _{GS} , I _D = 35mA , T _J =175°C	-	1.9	-		
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 18V, I _D = 75A	T _J =25°C	-	13	19	mΩ
			T _J =175°C	-	23	-	
Dynamic Characteristics							
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} = 1000V, f=100kHz, V _{GS} =0V	-	6893	-	pF	
Output Capacitance	C _{oss}		-	249	-		
Reverse Transfer Capacitance	C _{rss}		-	19	-		
Gate Resistance	R _G	f=1MHz	-	2.4	-	Ω	
Total Gate Charge	Q _g	V _{DS} =800V, I _D =75A V _{GS} =-4V/+18V	-	306	-	nC	
Gate-Source Charge	Q _{gs}		-	87	-		
Gate-Drain Charge	Q _{gd}		-	80	-		
Turn-on Delay Time	t _{d(on)}	V _{DD} =800V, V _{GS} =- 4/+18V, I _D =75A, R _{g(ext)} =2.5Ω, L=200μH	-	25	-	ns	
Turn-on Rise Time	t _r		-	37	-		
Turn-Off Delay Time	t _{d(off)}		-	57	-		
Turn-Off Fall Time	t _f		-	17	-		
Turn-On Energy	E _{on}	V _{DD} =800V, V _{GS} =- 4/+18V, I _D =75A, R _{g(ext)} =2.5Ω, L=200μH	-	1043	-	μJ	
Turn-Off Energy	E _{off}		-	828	-		

Electrical characteristics per line@25°C (unless otherwise specified)

Reverse Diode Characteristics							
Body Diode Forward Voltage	V_{SD}	$V_{GS}=-4V, I_{SD}=3.75A$	$T_J=25^{\circ}C$	-	3.9	-	V
			$T_J=175^{\circ}C$	-	3.3	-	
Continuous Diode Forward Current	I_S	$V_{GS}=-4V$	$T_c=25^{\circ}C$	-	150	-	A
			$T_c=100^{\circ}C$	-	82	-	
Reverse Recovery Time	t_{rr}	$V_{GS}=-4V, V_R=800V, I_D=75A, di/dt=7000A/\mu s$		-	15	-	ns
Reverse Recovery Charge	Q_{rr}			-	434	-	nC
Peak Reverse Recovery Current	I_{rrm}			-	51	-	A

Typical Characteristics

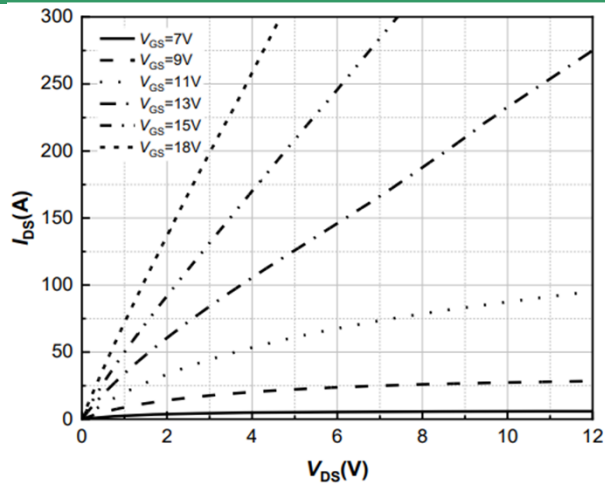


Figure 1. Output Characteristics
 $T_j = -40^\circ\text{C}$

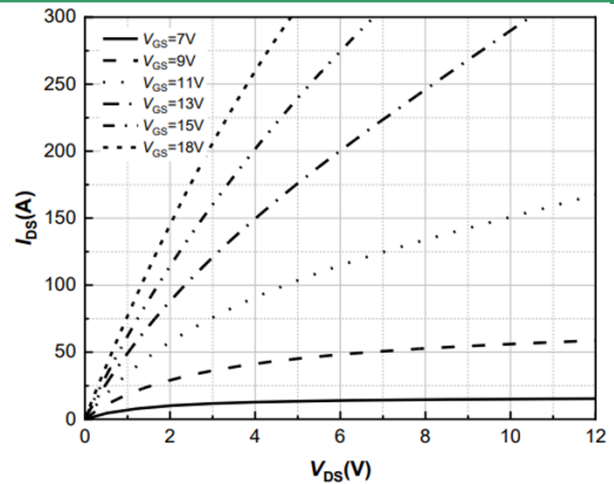


Figure 2. Output Characteristics
 $T_j = 25^\circ\text{C}$

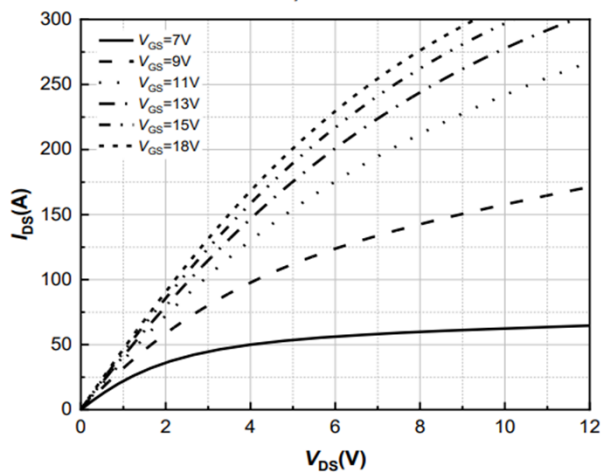


Figure 3. Output Characteristics
 $T_j = 175^\circ\text{C}$

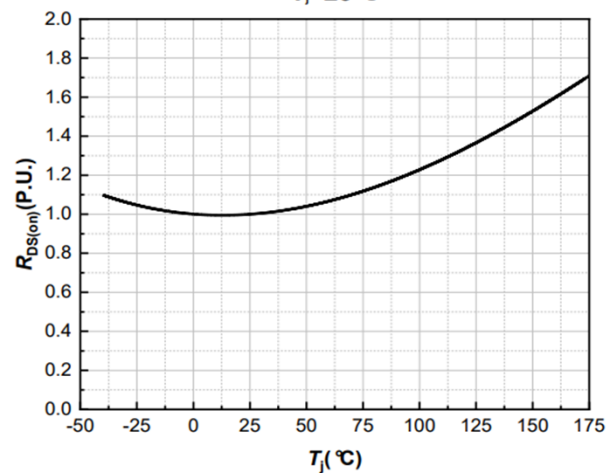


Figure 4. Normalized On-Resistance vs. Temperature

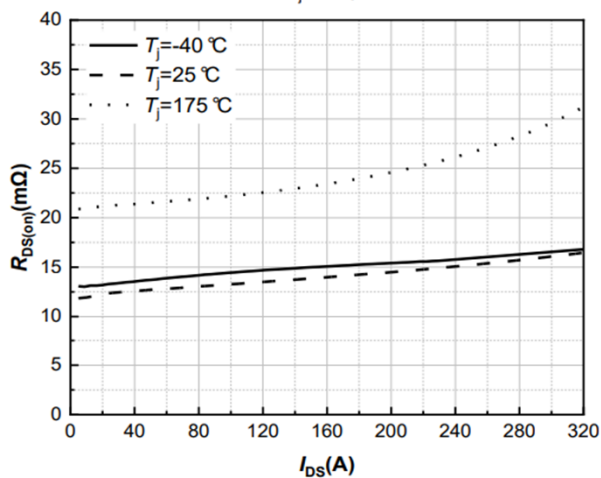


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

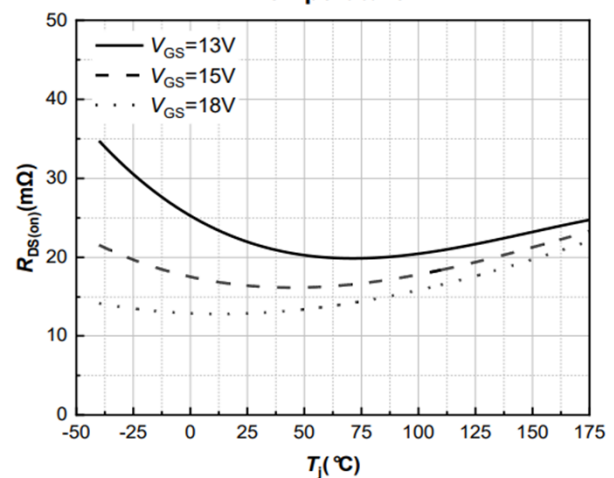


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

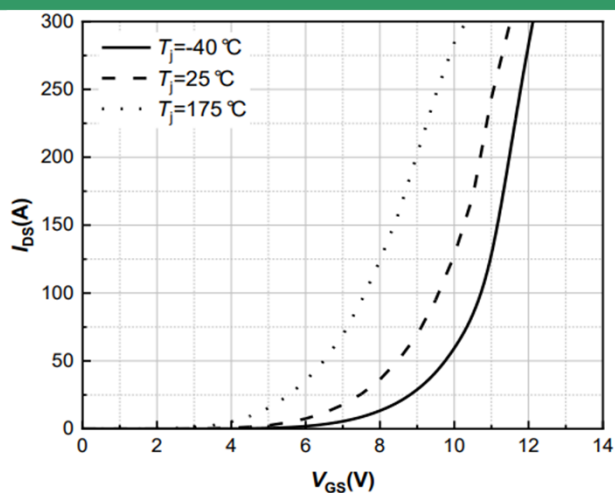


Figure 7. Transfer Characteristic for Various Junction Temperatures
 $V_{DS}=20V$

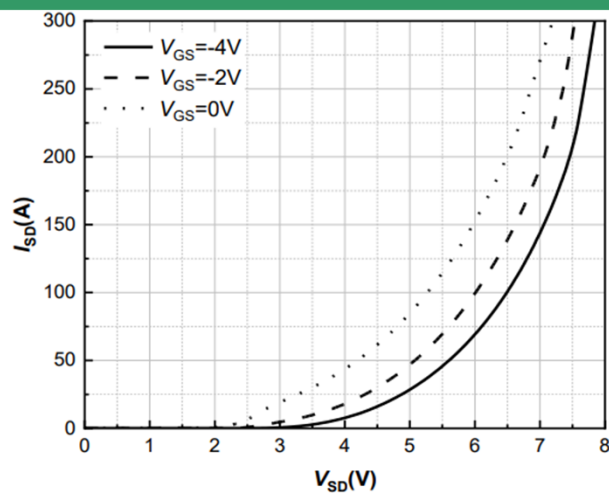


Figure 8. Body Diode Characteristic
 $T_J=-40^{\circ}C$

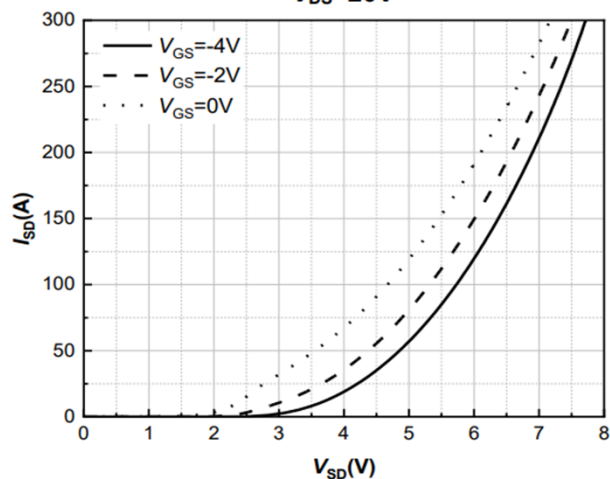


Figure 9. Body Diode Characteristic
 $T_J=25^{\circ}C$

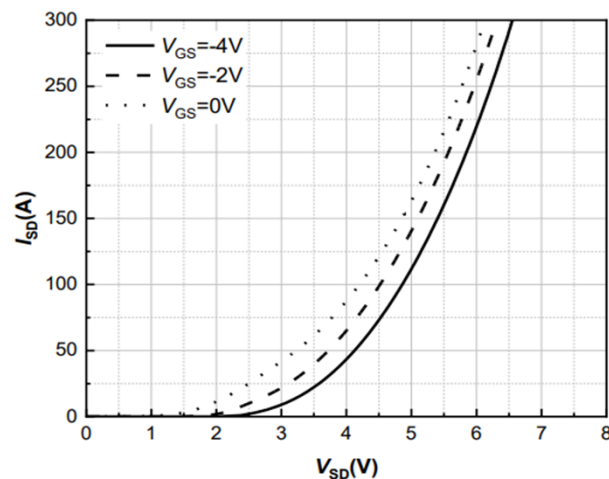


Figure 10. Body Diode Characteristic
 $T_J=175^{\circ}C$

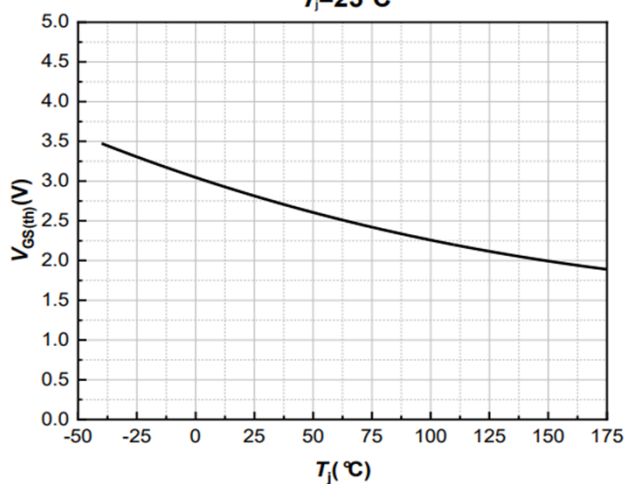


Figure 11. Threshold Voltage vs. Temperature

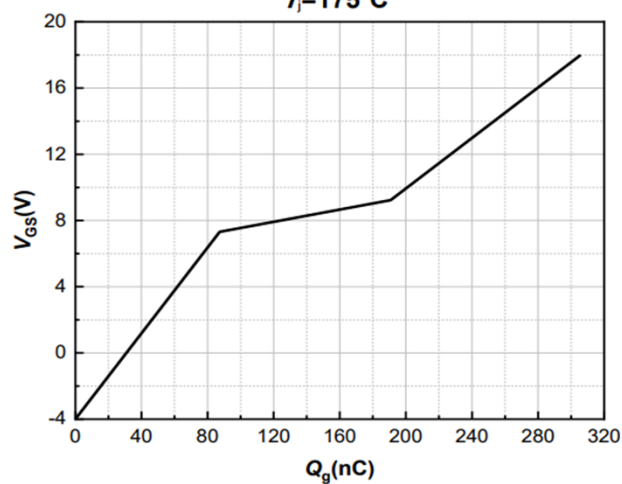


Figure 12. Gate Charge Characteristics

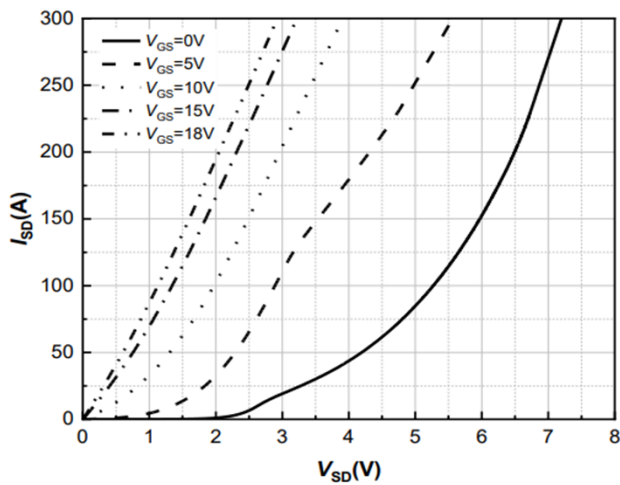


Figure 13. 3rd Quadrant Characteristic
 $T_j = -40^\circ\text{C}$

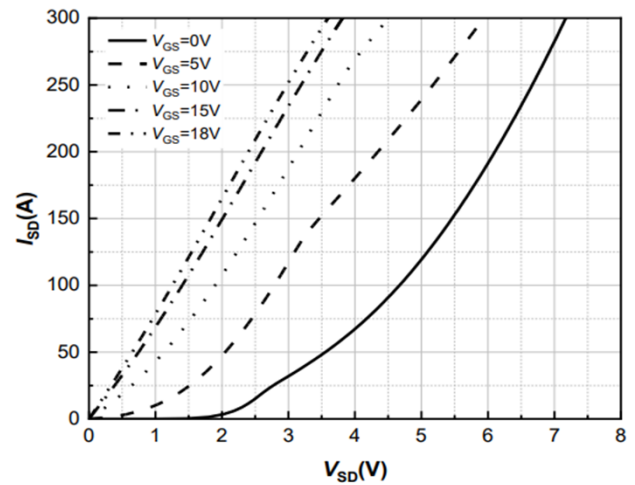


Figure 14. 3rd Quadrant Characteristic
 $T_j = 25^\circ\text{C}$

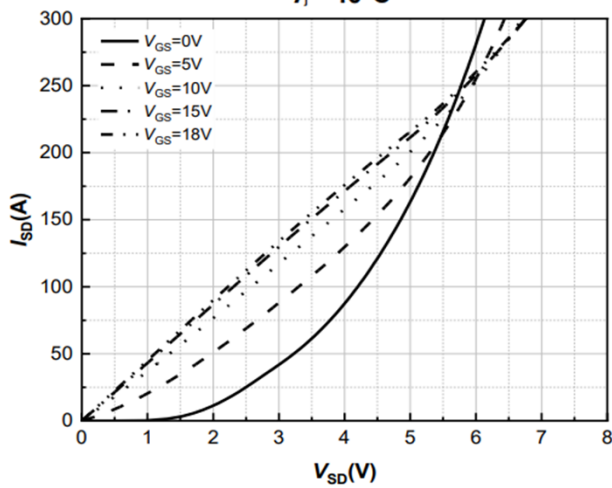


Figure 15. 3rd Quadrant Characteristic
 $T_j = 175^\circ\text{C}$

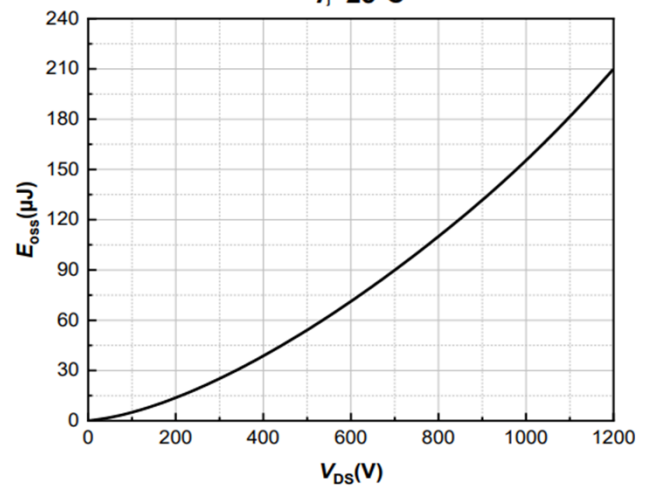


Figure 16. Output Capacitor Stored Energy

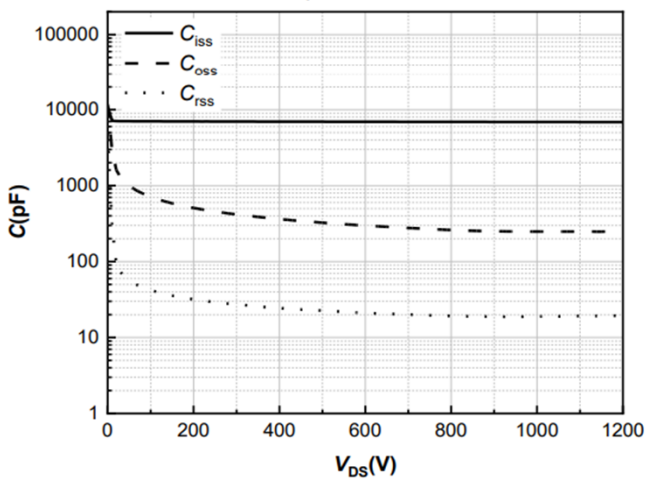


Figure 17. Capacitances vs. Drain-Source

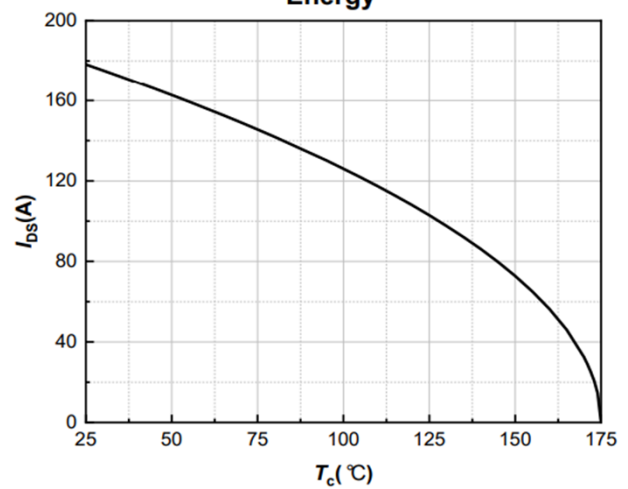


Figure 18. Continuous Drain Current Derating vs. Case Temperature

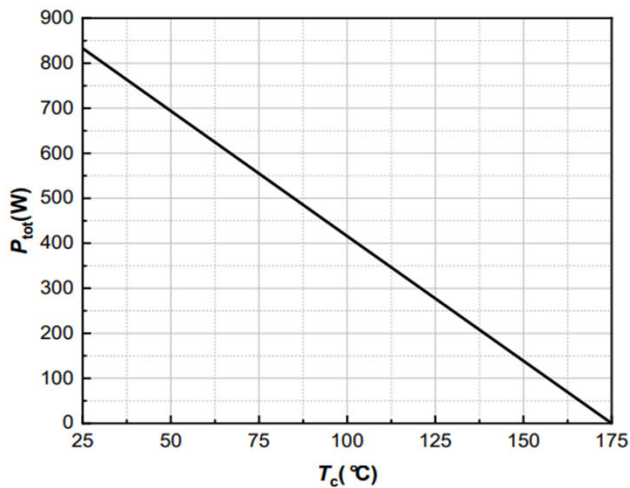


Figure 19. Maximum Power Dissipation Derating vs. Case Temperature

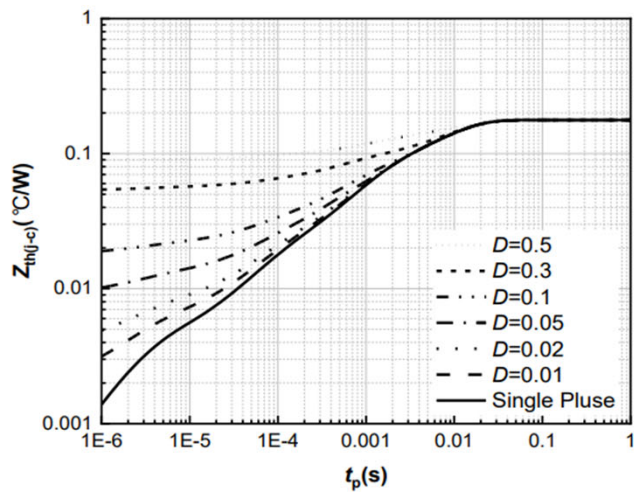


Figure 20. Transient Thermal Impedance

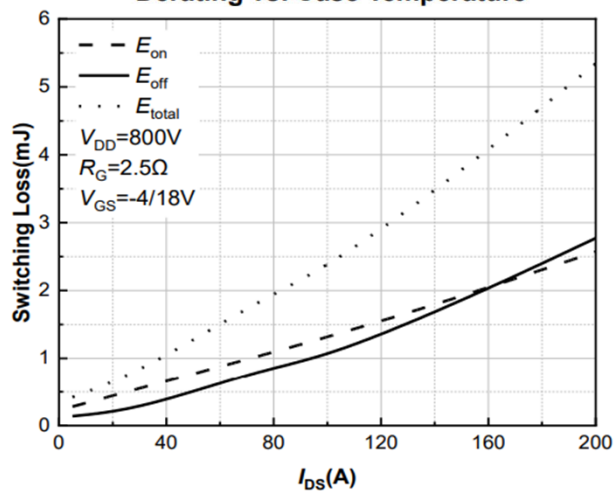


Figure 21. Clamped Inductive Switching Energy vs. Drain Current

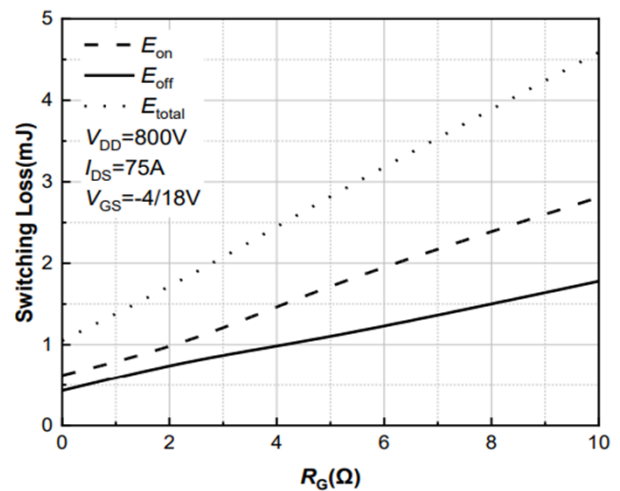


Figure 22. Clamped Inductive Switching Energy vs. R_G

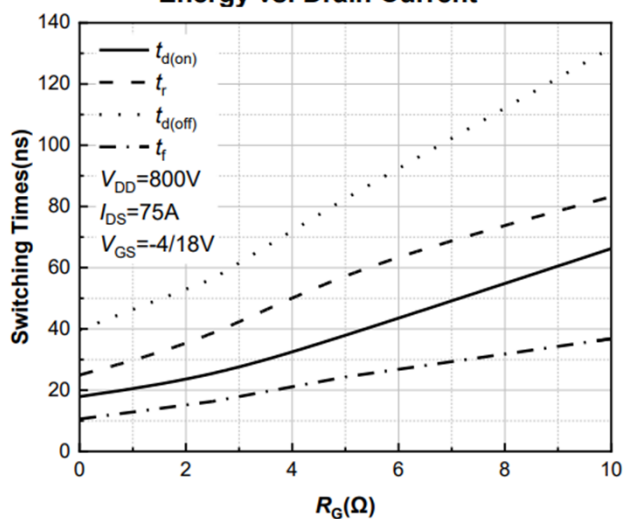


Figure 23. Switching Times vs. R_G

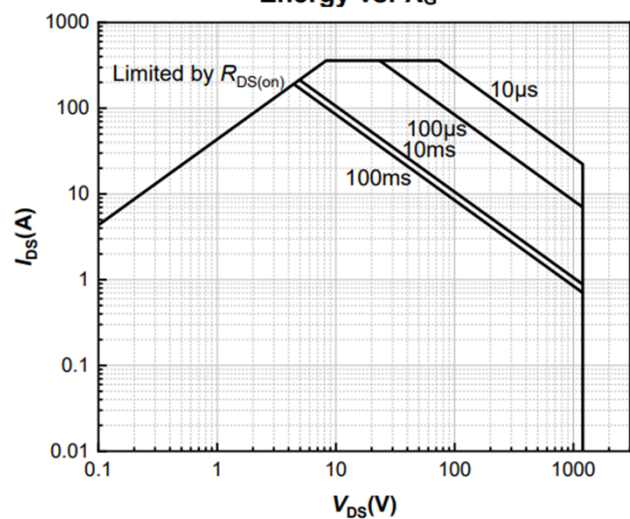
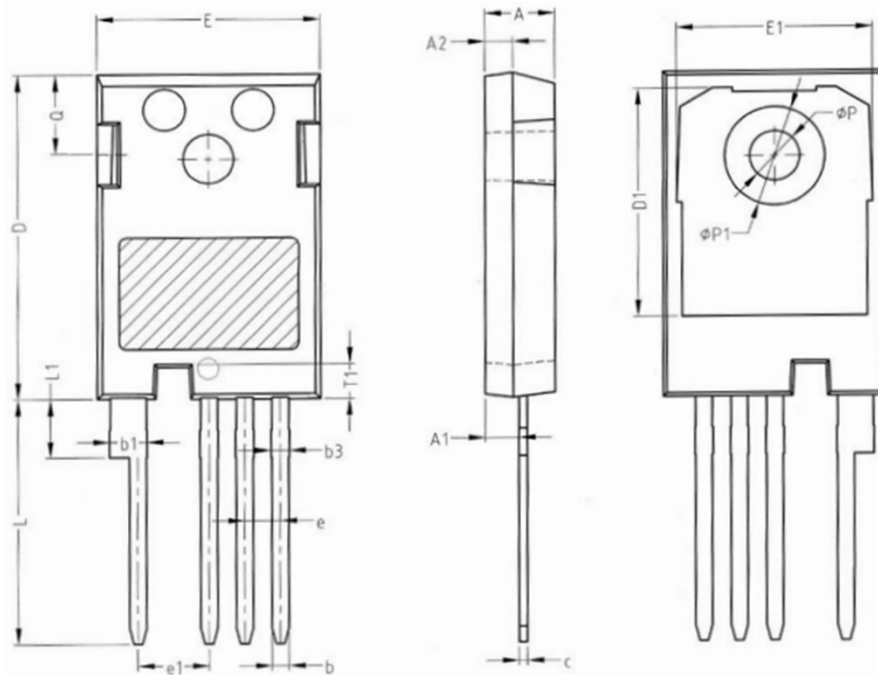


Figure 24. Safe Operating Area

Product dimension (TO-247-4L)



Dim	Millimeters		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.80	2.00	2.20
b	1.06	1.21	1.36
b1	2.33	2.63	2.93
b3	1.07	1.30	1.60
c	0.51	0.61	0.75
D	23.30	23.45	23.60
D1	16.25	16.55	16.85
E	15.74	15.94	16.14
E1	13.72	14.02	14.32
T1	2.35	2.50	2.65
e	2.54 BSC		
e1	5.08 BSC		
Q	5.49	5.79	6.09
L	17.27	17.57	17.87
L1	3.99	4.19	4.39
ΦP	3.40	3.60	3.80
ΦP1	7.19 REF		

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